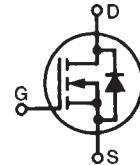


# PolarHV™ Power MOSFET

N-Channel Enhancement Mode  
Fast Recovery Diode  
Avalanche Rated

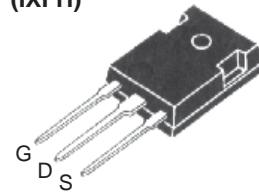
**IXFH26N60P**  
**IXFT26N60P**  
**IXFV26N60P**  
**IXFV26N60PS**

$V_{DSS} = 600$  V  
 $I_{D25} = 26$  A  
 $R_{DS(on)} \leq 270$  mΩ  
 $t_{rr} \leq 200$  ns

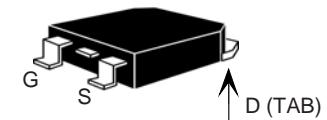


Symbol	Test Conditions	Maximum Ratings		
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	600	V	
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1\text{ M}\Omega$	600	V	
$V_{GSS}$	Continuous	$\pm 30$	V	
$V_{GSM}$	Transient	$\pm 40$	V	
$I_{D25}$	$T_c = 25^\circ\text{C}$	26	A	
$I_{DM}$	$T_c = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	65	A	
$I_{AR}$	$T_c = 25^\circ\text{C}$	13	A	
$E_{AR}$	$T_c = 25^\circ\text{C}$	40	mJ	
$E_{AS}$	$T_c = 25^\circ\text{C}$	1.2	J	
$dv/dt$	$I_s \leq I_{DM}$ , $di/dt \leq 100\text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$ , $R_G = 5\Omega$	10	V/ns	
$P_D$	$T_c = 25^\circ\text{C}$	460	W	
$T_J$		-55 ... +150	°C	
$T_{JM}$		150	°C	
$T_{stg}$		-55 ... +150	°C	
$T_L$	1.6 mm (0.062 in.) from case for 10 s	300	°C	
$T_{SOLD}$	Plastic body for 10 s	260	°C	
$M_d$	Mounting torque (TO-3P&TO-247)	1.13/10	Nm/lb.in.	
$F_c$	Mounting force (PLUS220)	11..65/2.5..15	N/lb	
<b>Weight</b>	TO-247	6.0	g	
	TO-268	5.0	g	
	PLUS220 & PLUS220SMD	4.0	g	

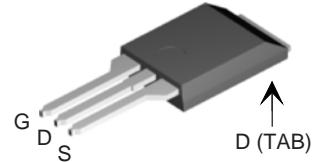
TO-247 (IXFH)



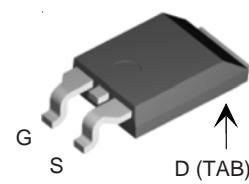
TO-268 (IXFT)



PLUS220 (IXFV)



PLUS220SMD (IXFV...S)



G = Gate  
S = Source

D = Drain  
TAB = Drain

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4\text{ mA}$	2.5		5.0 V
$I_{GSS}$	$V_{GS} = \pm 30\text{ V}$ , $V_{DS} = 0\text{ V}$		$\pm 100$	nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0\text{ V}$		25 250	$\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300\text{ }\mu\text{s}$ , duty cycle $d \leq 2\%$		270	mΩ

## Features

- Fast Recovery diode
- Unclamped Inductive Switching (UIS) rated
- International standard packages
- Low package inductance
  - easy to drive and to protect

## Advantages

- Easy to mount
- Space savings
- High power density

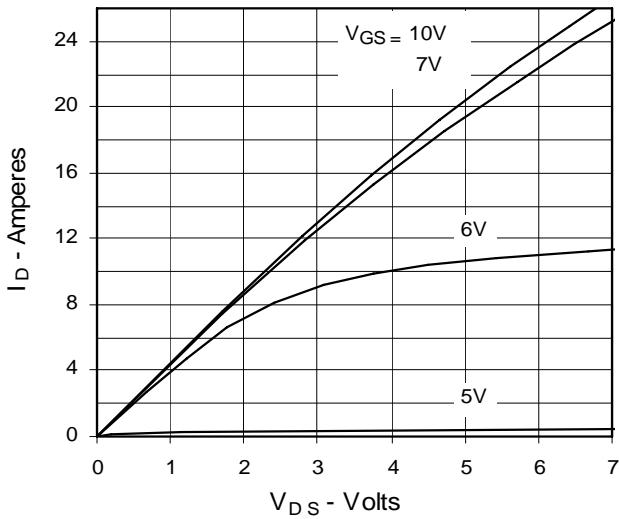
Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)	Min.	Typ.
$g_{fs}$	$V_{DS} = 20\text{ V}; I_D = 0.5 I_{D25}$ , pulse test	16	26	S
$C_{iss}$ $C_{oss}$ $C_{rss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	4150		pF
		400		pF
		27		pF
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 I_{D25}$ $R_G = 5\Omega$ (External)	25		ns
		27		ns
		75		ns
		21		ns
$Q_{g(on)}$ $Q_{gs}$ $Q_{gd}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$	72		nC
		27		nC
		24		nC
$R_{thJC}$			0.27	°C/W
$R_{thCs}$	(PLUS220 & TO-247)	0.21		°C/W

Symbol	Test Conditions	Characteristic Values			
		(T <sub>J</sub> = 25°C, unless otherwise specified)	Min.	Typ.	Max.
$I_s$	$V_{GS} = 0\text{ V}$			26	A
$I_{SM}$	Repetitive			78	A
$V_{SD}$	$I_F = I_s, V_{GS} = 0\text{ V}$ , pulse test			1.5	V
$t_{rr}$ $I_{RM}$ $Q_{RM}$	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}; V_{GS} = 0\text{ V}$	150	200	ns	
		7		A	
		0.7		μC	

### Characteristic Curves

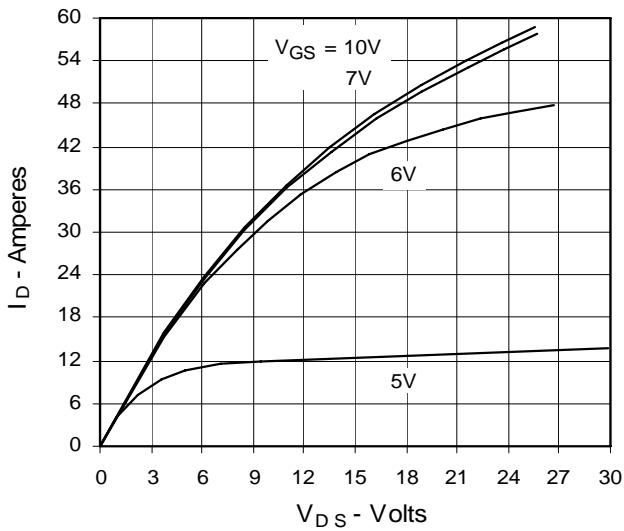
**Fig. 1. Output Characteristics**

@ 25°C



**Fig. 2. Extended Output Characteristics**

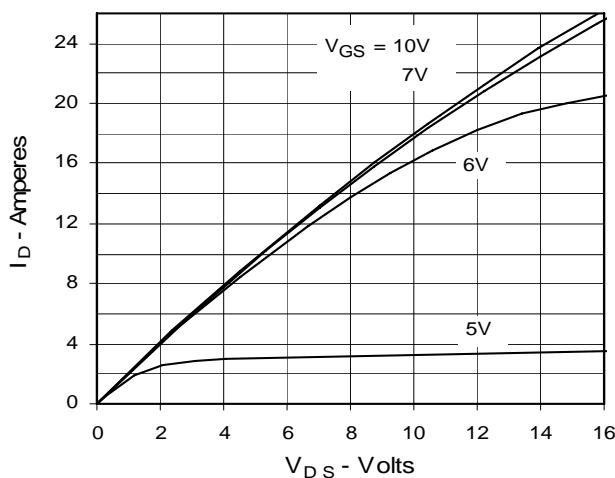
@ 25°C



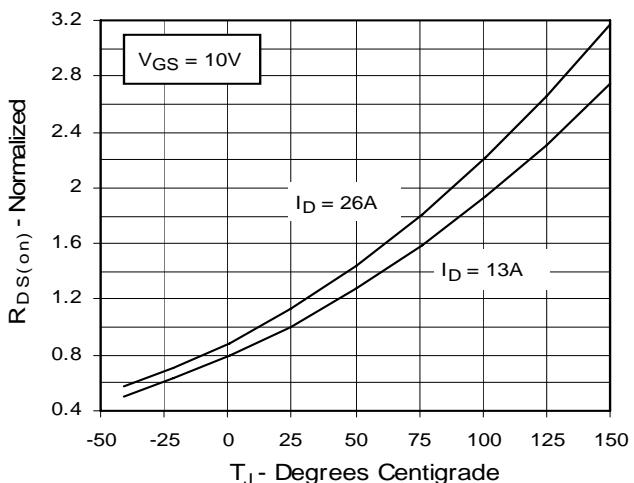
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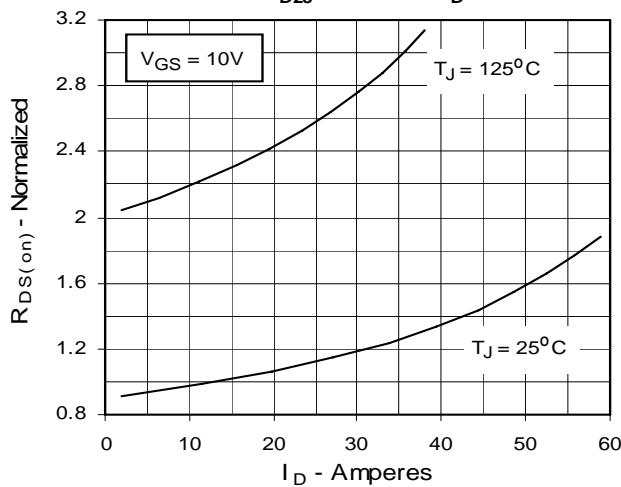
**Fig. 3. Output Characteristics  
@ 125°C**



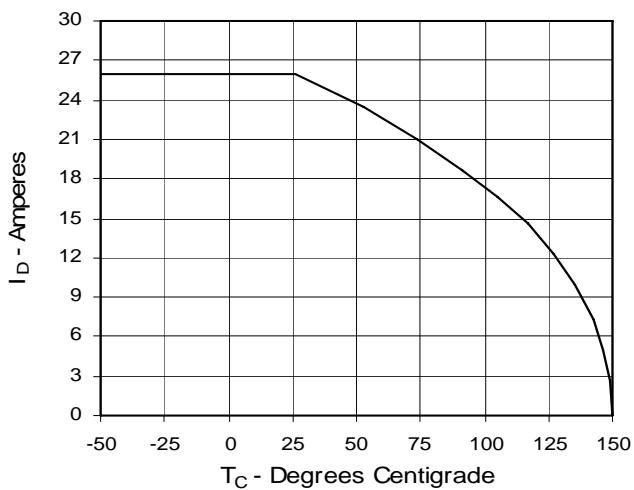
**Fig. 4.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs. Junction Temperature**



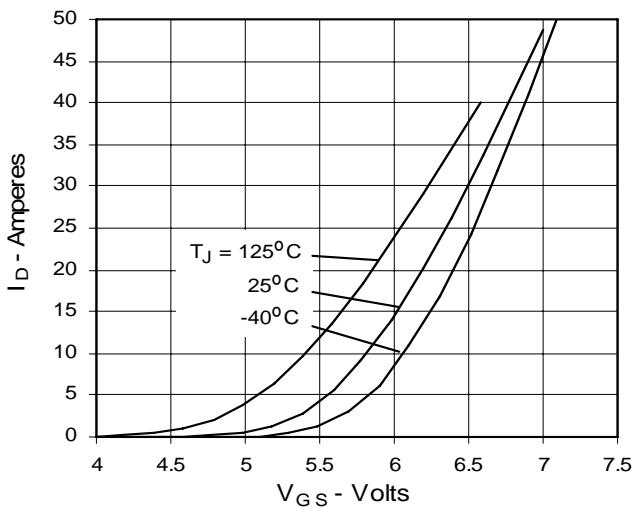
**Fig. 5.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs.  $I_D$**



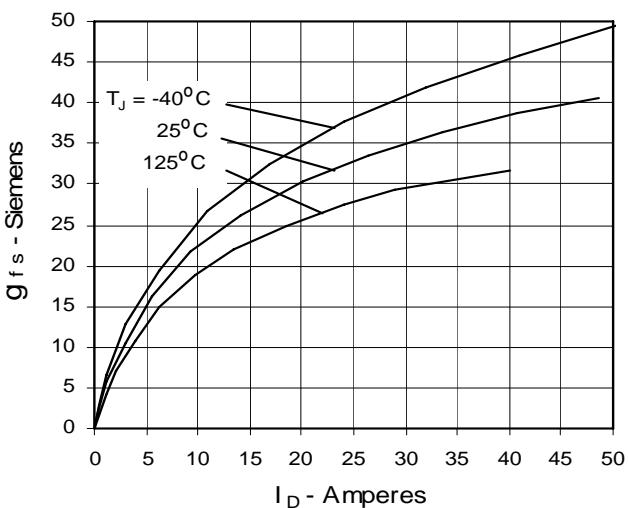
**Fig. 6. Drain Current vs. Case Temperature**



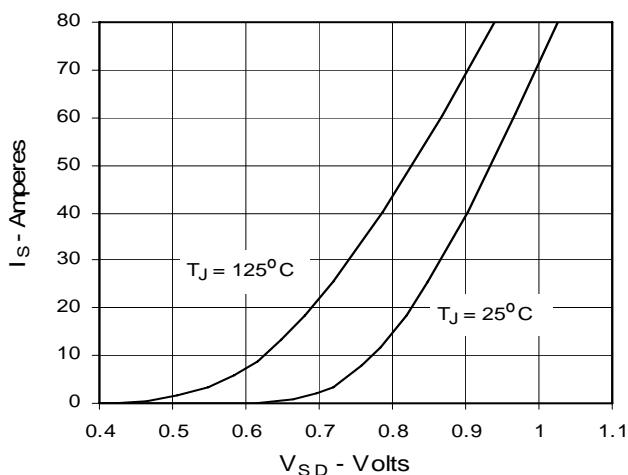
**Fig. 7. Input Admittance**



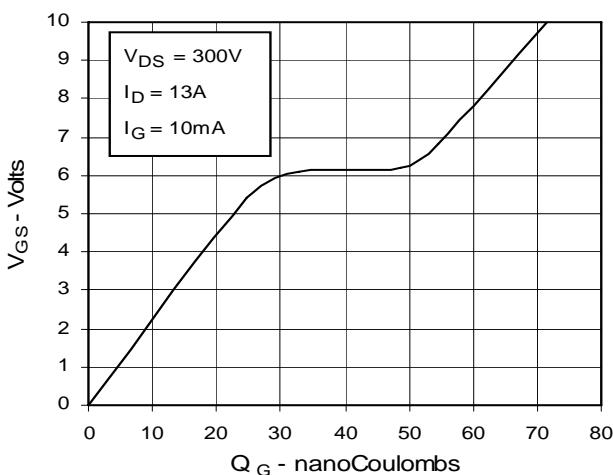
**Fig. 8. Transconductance**



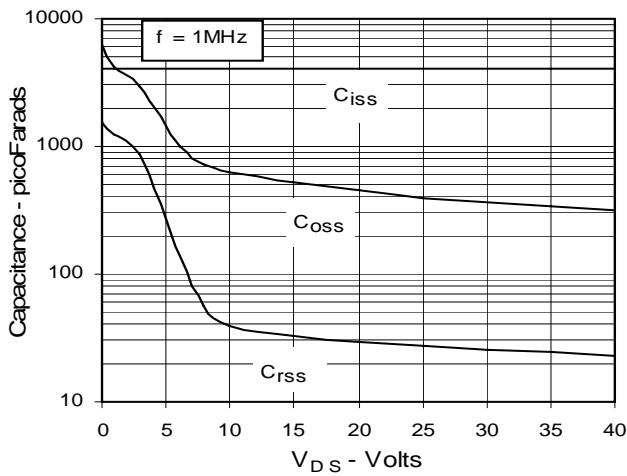
**Fig. 9. Source Current vs.  
Source-To-Drain Voltage**



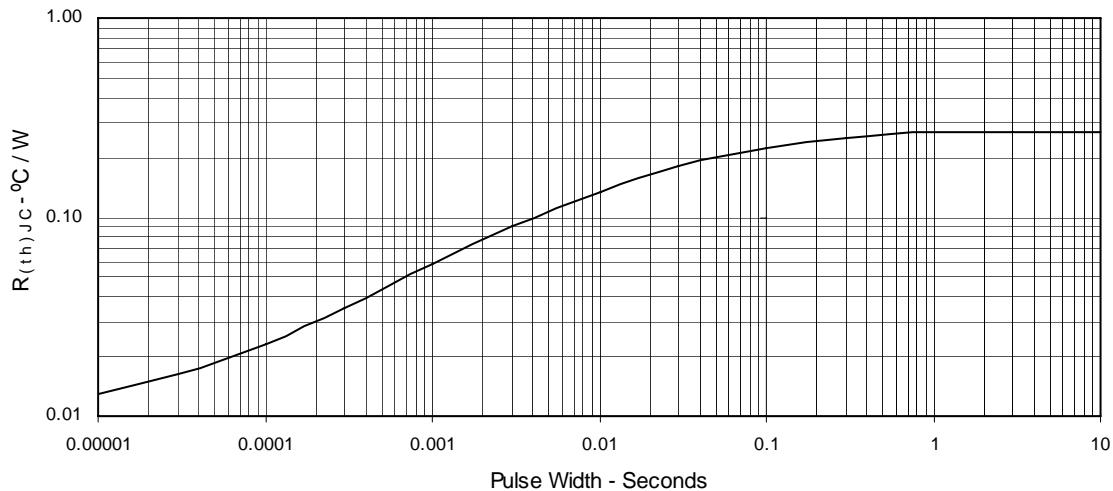
**Fig. 10. Gate Charge**

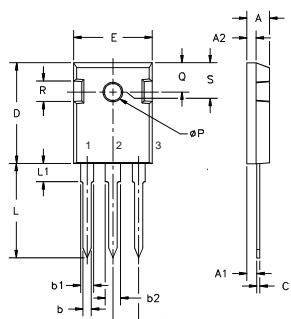


**Fig. 11. Capacitance**

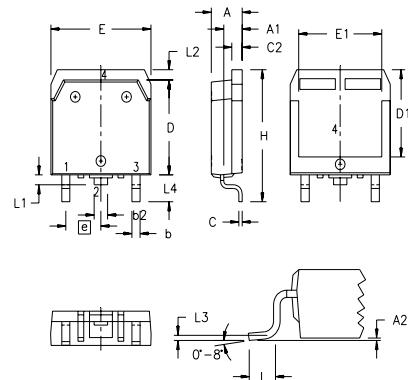


**Fig. 12. Maximum Transient Thermal Resistance**

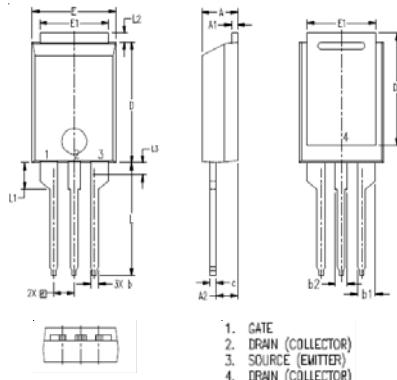


**TO-247 AD (IXFH) Outline**


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L <sub>1</sub>		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

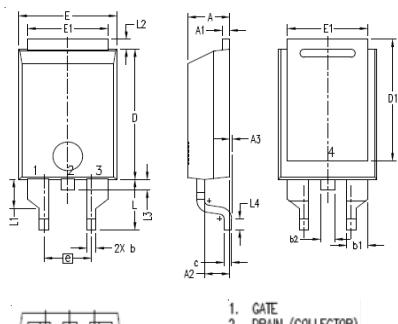
**TO-268 (IXFT) Outline**


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A <sub>1</sub>	.106	.114	2.70	2.90
A <sub>2</sub>	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b <sub>2</sub>	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C <sub>2</sub>	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D <sub>1</sub>	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E <sub>1</sub>	.524	.535	13.30	13.60
e	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L <sub>1</sub>	.047	.055	1.20	1.40
L <sub>2</sub>	.039	.045	1.00	1.15
L <sub>3</sub>	.010	BSC	0.25	BSC
L <sub>4</sub>	.150	.161	3.80	4.10

**PLUS220 (IXFV) Outline**


1. GATE
2. DRAIN (COLLECTOR)
3. SOURCE (EMITTER)
4. DRAIN (COLLECTOR)

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A <sub>1</sub>	.028	.035	0.70	0.90
A <sub>2</sub>	.098	.118	2.50	3.00
b	.035	.047	0.90	1.20
b <sub>1</sub>	.080	.095	2.03	2.41
b <sub>2</sub>	.054	.064	1.37	1.63
c	.028	.035	0.70	0.90
D	.551	.591	14.00	15.00
D <sub>1</sub>	.512	.539	13.00	13.70
E	.394	.433	10.00	11.00
E <sub>1</sub>	.331	.346	8.40	8.80
e	.100	BSC	2.54	BSC
L	.512	.551	13.00	14.00
L <sub>1</sub>	.118	.138	3.00	3.50
L <sub>2</sub>	.035	.051	0.90	1.30
L <sub>3</sub>	.047	.059	1.20	1.50

**PLUS220SMD (IXFV\_S) Outline**


1. GATE
2. DRAIN (COLLECTOR)
3. SOURCE (EMITTER)
4. DRAIN (COLLECTOR)

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A <sub>1</sub>	.028	.035	0.70	0.90
A <sub>2</sub>	.098	.118	2.50	3.00
A <sub>3</sub>	.000	.010	0.00	0.25
b	.035	.047	0.90	1.20
b <sub>1</sub>	.080	.095	2.03	2.41
b <sub>2</sub>	.054	.064	1.37	1.63
c	.028	.035	0.70	0.90
D	.551	.591	14.00	15.00
D <sub>1</sub>	.512	.539	13.00	13.70
E	.394	.433	10.00	11.00
E <sub>1</sub>	.331	.346	8.40	8.80
e	.200	BSC	5.08	BSC
L	.209	.228	5.30	5.80
L <sub>1</sub>	.118	.138	3.00	3.50
L <sub>2</sub>	.035	.051	0.90	1.30
L <sub>3</sub>	.047	.059	1.20	1.50
L <sub>4</sub>	.039	.059	1.00	1.50



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